

## **isc Silicon NPN Power Transistor**

# INCHANGE SEMICONDUCTOR

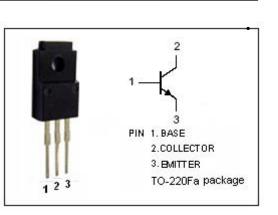
2SC3979

### DESCRIPTION

- · Collector-Base Breakdown Voltage-: V<sub>(BR)CBO</sub>= 900V(Min.)
- Wide Area of Safe Operation
- · High Speed Switching
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

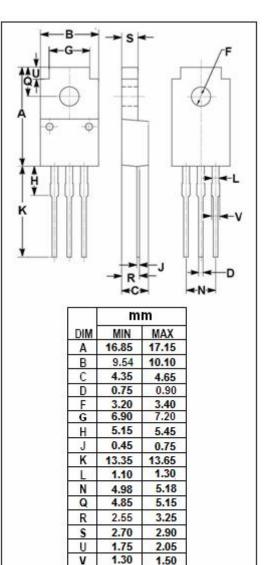
### **APPLICATIONS**

• Designed for high speed switching applications.



#### ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	900	v	
V <sub>CES</sub>	Collector-Emitter Voltage	900	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
Ιc	Collector Current-Continuous	3	А	
I <sub>CM</sub>	Collector Current-Peak	5	A	
Ι <sub>Β</sub>	Base Current-Continuous	1	A	
Pc	Collector Power Dissipation @T₂=25℃	2		
	Collector Power Dissipation @T <sub>C</sub> =25℃	40	W	
Tj	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	





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## ELECTRICAL CHARACTERISTICS

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!^{\circ}\!\!^{\circ}_{\operatorname{C}}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	800			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 0.8A; I <sub>B</sub> = 0.16A			1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 0.8A; I <sub>B</sub> = 0.16A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 900V; I <sub>E</sub> = 0			50	μA
Іево	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			50	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	8			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 0.8A; V <sub>CE</sub> = 5V	6			
f⊤	Current-Gain—Bandwidth Product	Ic= 0.15A; Vce= 5V; f= 1MHz		10		MHz

Switching Times

t <sub>on</sub>	Turn-on Time			0.7	μ <b>S</b>
ts	Storage Time	I <sub>C</sub> = 0.8A; I <sub>B1</sub> = 0.16A; I <sub>B2</sub> = -0.32A; V <sub>CC</sub> = 250V		2.5	μ <b>S</b>
t <sub>f</sub>	Fall Time			0.3	μ <b>S</b>

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